

4. (Amended) The layer system according to claim 3, characterized in that the oxide layers contain about 90-95% indium and about 5-10% cerium.

5. (Amended) The layer system according to claim 4, characterized in that the silver layer contains up to 10 wt. % copper.

6. (Amended) The layer system according to claim 1, characterized in that the layer system is less than 100 nm thick, with the silver layer being less than 20 nm thick, and the two oxide layers being less than 50 nm thick.

7. (Amended) The layer system according to claim 6, characterized in that the oxide layers contain about 90-95% indium and about 5-10% cerium.

8. (Amended) The layer system according to claim 7, characterized in that the silver layer contains up to 10 wt. % copper.

9. (Amended) The layer system according to claim 1, characterized in that the oxide layers contain about 90-95% indium and about 5-10% cerium.

10. (Amended) The layer system according to claim 9, characterized in that the silver layer contains up to 10 wt. % copper.

11. (Amended) The layer system according to claim 1, characterized in that the silver layer contains up to 10 wt. % ~~copper~~.

12. (Amended) The layer system according to claim 1 in which the second oxide layer is deposited by means of pulsed DC sputtering or AC-superimposed DC sputtering.

~~13~~ 22. (Amended) The layer system of claim 1, characterized in that the frequency of the superimposed AC is between 1 and 50 MHz.

~~14~~ 23. (Amended) The layer system of claim 1, characterized in that the AC component, defined by the ratio of the DC and AC power supplies, is between 10-90%.

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cont. ~~15~~ 24. (Amended) The layer system of claim 1, characterized in that the total power density (AC and DC) is in the range from 1-3 W/cm².

~~16~~ 25. (Amended) The layer system of claim ~~1~~ ²⁴, characterized in that magnetron sputtering is chosen as sputtering method.
